DMG204B1

Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For low frequency amplification

■ Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage V_{CE(sat)}
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C5

■ Basic Part Number

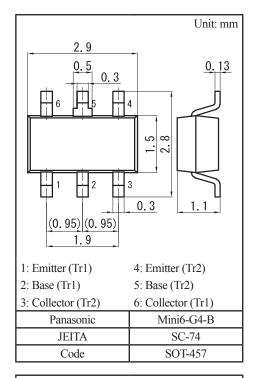
DSC2501 + DSA2001 (Individual)

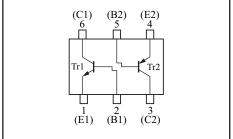
Packaging

DMG204B10R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V _{CBO}	25	V
	Collector-emitter voltage (Base open)	V _{CEO}	20	V
	Emitter-base voltage (Collector open)	V _{EBO}	12	V
	Collector current	I_{C}	0.5	A
	Peak collector current	I _{CP}	1	A
Tr2	Collector-base voltage (Emitter open)	V _{CBO}	-60	V
	Collector-emitter voltage (Base open)	V _{CEO}	-50	V
	Emitter-base voltage (Collector open)	V _{EBO}	-7	V
	Collector current	I_{C}	-100	mA
	Peak collector current	I_{CP}	-200	mA
	Total power dissipation	P _T	300	mW
Overall	Junction temperature	T_j	150	°C
	Operating ambient temperature	T _{opr}	-40 to +85	°C
	Storage temperature	T _{stg}	-55 to +150	°C





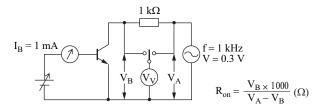
■ Electrical Characteristics $T_a = 25$ °C±3°C

• Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 10 \mu A, I_E = 0$	25			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	12			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 25 \text{ V}, I_{E} = 0$			100	nA
Forward current transfer ratio	h _{FE}	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}$	200		800	_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = 0.5 \text{ A}, I_B = 20 \text{ mA}$		0.18	0.40	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = 0.5 \text{ A}, I_B = 50 \text{ mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6		pF
ON resistance *2	R _{on}			1.0		Ω

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. *1: Pulse measurement
 - *2: Ron measurement circuit



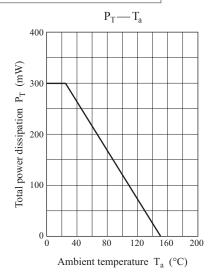
• Tr2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu \text{A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = -10 \mu A, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\rm CB} = -20 \text{ V}, I_{\rm E} = 0$			-0.1	μА
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -10 \text{ V}, I_{B} = 0$			-100	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	210		460	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		- 0.2	-0.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2		pF

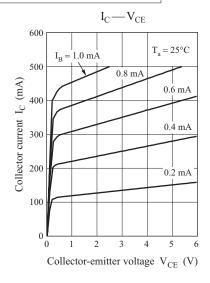
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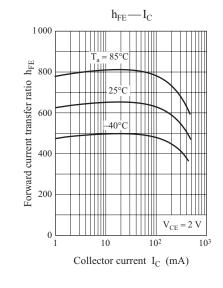
Ver. CED 2

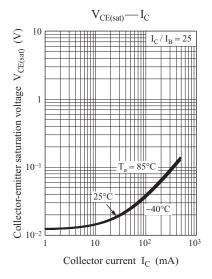
Common characteristics chart

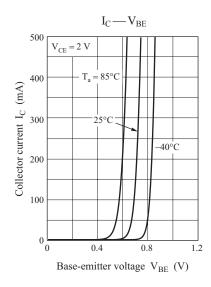


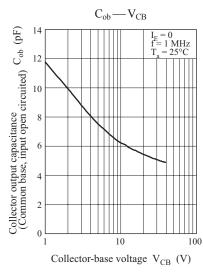
Characteristics charts of Tr1

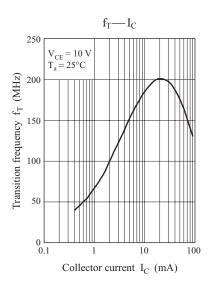


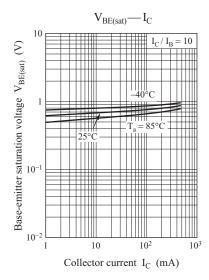




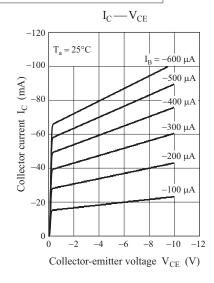


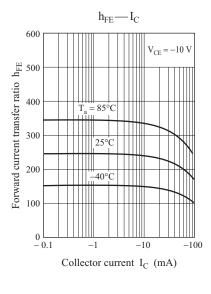


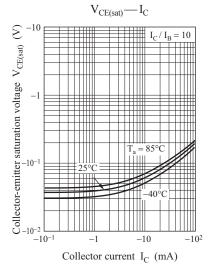


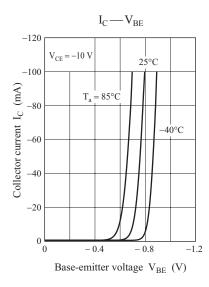


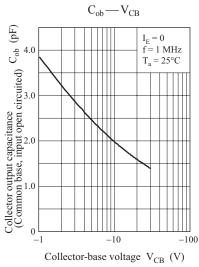
Characteristics charts of Tr2

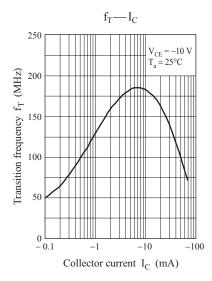






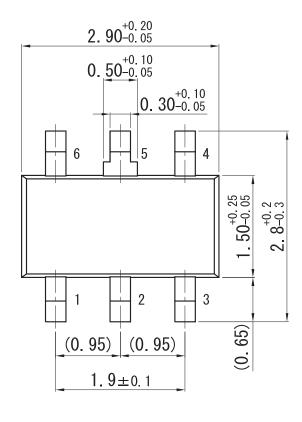


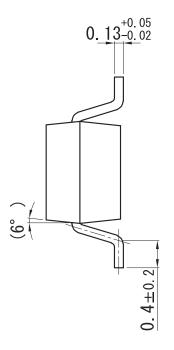


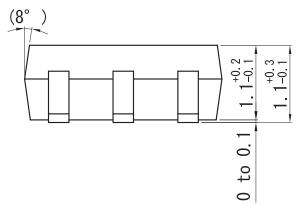


Mini6-G4-B

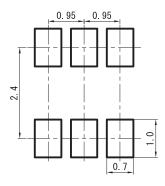
Unit: mm







■ Land Pattern (Reference) (Unit: mm)



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